

# Complementary Bipolar Power Transistors MJL3281A (NPN) MJL1302A (PNP)

### **Features**

- Exceptional Safe Operating Area
- NPN/PNP Gain Matching within 10% from 50 mA to 5 A
- Excellent Gain Linearity
- High BVCEO
- · High Frequency
- These Devices are Pb-Free and are RoHS Compliant\*

### **Benefits**

- Reliable Performance at Higher Powers
- Symmetrical Characteristics in Complementary Configurations
- Accurate Reproduction of Input Signal
- Greater Dynamic Range
- High Amplifier Bandwidth

# **Applications**

- High-End Consumer Audio Products
  - ♦ Home Amplifiers
  - ♦ Home Receivers
- Professional Audio Amplifiers
  - ◆ Theater and Stadium Sound Systems
  - ◆ Public Address Systems (PAs)

# MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	260	Vdc
Collector-Base Voltage	$V_{CBO}$	260	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc
Collector-Emitter Voltage - 1.5 V	V <sub>CEX</sub>	260	Vdc
Collector Current - Continuous	I <sub>C</sub>	15	Adc
Collector Current - Peak (Note 1)	I <sub>CM</sub>	25	Adc
Base Current - Continuous	Ι <sub>Β</sub>	1.5	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate Above 25°C	P <sub>D</sub>	200 1.43	Watts W/°C
Operating and Storage Junction Temperature Range	$T_J$ , $T_{stg}$	– 65 to +150	°C

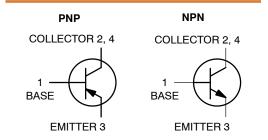
# THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.625	°C/W

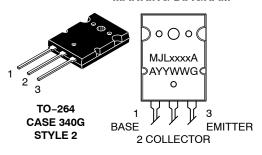
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle < 10%.

# 15 AMPERES COMPLEMENTARY SILICON POWER TRANSISTORS 260 VOLTS 200 WATTS



# **MARKING DIAGRAM**



xxxx = 3281 or 1302
A = Location Code
YY = Year
WW = Work Week
G = Pb-Free Package

# **ORDERING INFORMATION**

Device	Package	Shipping
MJL3281AG	TO-264 (Pb-Free)	25 Units/Rail
MJL1302AG	TO-264 (Pb-Free)	25 Units/Rail

\*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

# MJL3281A (NPN) MJL1302A (PNP)

# **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage ( $I_C = 100 \text{ mAdc}, I_B = 0$ )	V <sub>CEO(sus)</sub>	260	-	Vdc
Collector Cutoff Current (V <sub>CB</sub> = 260 Vdc, I <sub>E</sub> = 0)	Ісво	-	50	μAdc
Emitter Cutoff Current $(V_{EB} = 5 \text{ Vdc}, I_C = 0)$	I <sub>EBO</sub>	-	5	μAdc
SECOND BREAKDOWN				
Second Breakdown Collector with Base Forward Biased $(V_{CE} = 50 \text{ Vdc}, t = 1 \text{ s (non-repetitive)} $ $(V_{CE} = 100 \text{ Vdc}, t = 1 \text{ s (non-repetitive)}$	I <sub>S/b</sub>	4 1	- -	Adc
ON CHARACTERISTICS				
DC Current Gain ( $I_C = 500 \text{ mAdc}$ , $V_{CE} = 5 \text{ Vdc}$ ) ( $I_C = 1 \text{ Adc}$ , $V_{CE} = 5 \text{ Vdc}$ ) ( $I_C = 3 \text{ Adc}$ , $V_{CE} = 5 \text{ Vdc}$ ) ( $I_C = 5 \text{ Adc}$ , $V_{CE} = 5 \text{ Vdc}$ ) ( $I_C = 6 \text{ Adc}$ , $V_{CE} = 5 \text{ Vdc}$ ) ( $I_C = 8 \text{ Adc}$ , $V_{CE} = 5 \text{ Vdc}$ )	h <sub>FE</sub>	75 75 75 75 75 45	150 150 150 150 150	
Collector–Emitter Saturation Voltage ( $I_C = 10$ Adc, $I_B = 1$ Adc)	V <sub>CE(sat)</sub>	-	3	Vdc
DYNAMIC CHARACTERISTICS				
Current-Gain - Bandwidth Product $(I_C = 1 \text{ Adc}, V_{CE} = 5 \text{ Vdc}, f_{test} = 1 \text{ MHz})$	f <sub>T</sub>	30	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)	C <sub>ob</sub>	-	600	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be

indicated by the Electrical Characteristics if operated under different conditions.

# MJL3281A (NPN) MJL1302A (PNP)

# **TYPICAL CHARACTERISTICS**

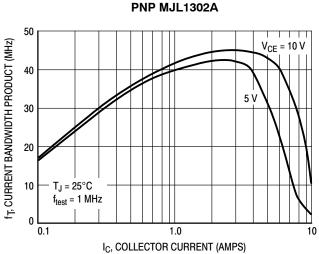


Figure 1. Typical Current Gain
Bandwidth Product

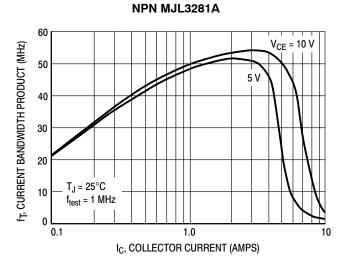


Figure 2. Typical Current Gain Bandwidth Product

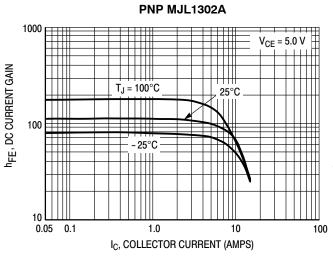


Figure 3. DC Current Gain

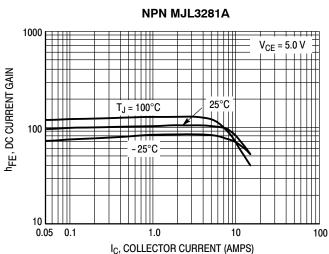


Figure 4. DC Current Gain

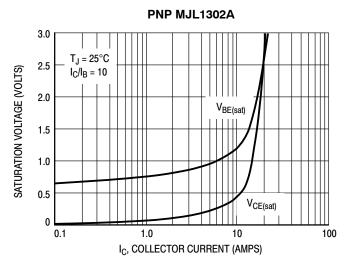


Figure 5. Typical Saturation Voltages

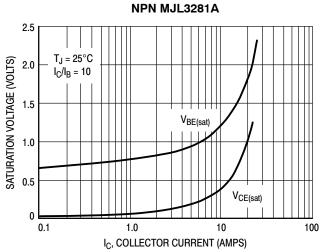


Figure 6. Typical Saturation Voltages

# **MJL3281A (NPN) MJL1302A (PNP)**

# TYPICAL CHARACTERISTICS

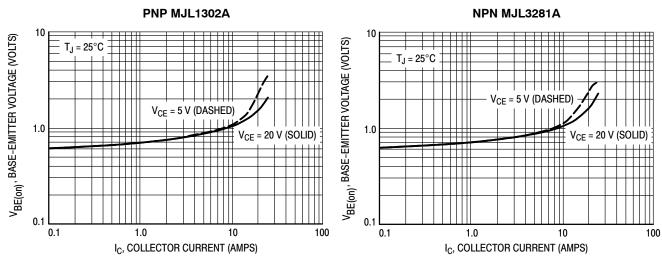


Figure 7. Typical Base-Emitter Voltage

Figure 8. Typical Base-Emitter Voltage

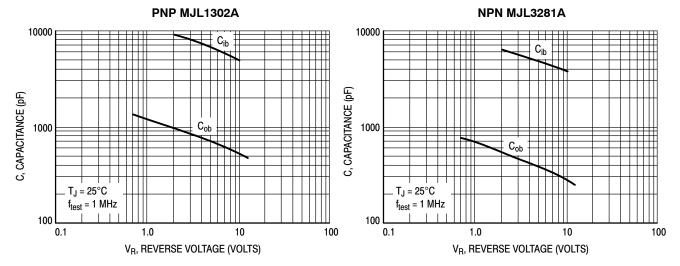


Figure 9. MJL1302A Typical Capacitance

Figure 10. MJL3281A Typical Capacitance

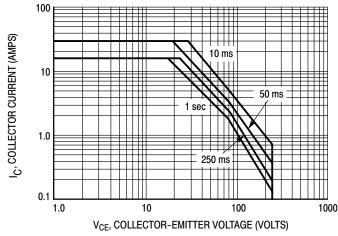
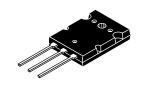


Figure 11. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 11 is based on  $T_{J(pk)} = 150^{\circ}\text{C}$ ;  $T_{C}$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.

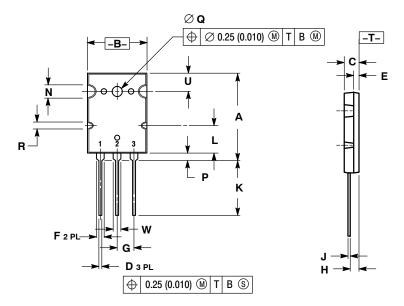




TO-3BPL (TO-264) CASE 340G-02 **ISSUE J** 

**DATE 17 DEC 2004** 

# SCALE 1:2



### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	28.0	29.0	1.102	1.142	
В	19.3	20.3	0.760	0.800	
С	4.7	5.3	0.185	0.209	
D	0.93	1.48	0.037	0.058	
E	1.9	2.1	0.075	0.083	
F	2.2	2.4	0.087	0.102	
G	5.45	5.45 BSC		0.215 BSC	
Н	2.6	3.0	0.102	0.118	
J	0.43	0.78	0.017	0.031	
K	17.6	18.8	0.693	0.740	
L	11.2 REF		0.411	REF	
N	4.35 REF		0.172	REF	
P	2.2	2.6	0.087	0.102	
Q	3.1	3.5	0.122	0.137	
R	2.25 REF		0.089	REF	
U	6.3 REF		0.248	REF	
W	2.8	3.2	0.110	0.125	

# **GENERIC MARKING DIAGRAM\***

STYLE 1	:
PIN 1.	GATE
2.	DRAIN
3.	SOURCE

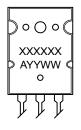
STYLE 2: PIN 1. BASE 2. COLLECTOR

EMITTER

STYLE 3: PIN 1. GATE 2. SOURCE DRAIN

STYLE 4: PIN 1. DRAIN 2. SOURCE GATE 3.

STYLE 5: PIN 1. GATE 2. COLLECTOR EMITTER



XXXXXX = Specific Device Code

Α = Location Code

YY = Year WW = Work Week

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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